

## **Amendments to the specification**

Please amend the paragraph on page 1, lines 5-15, as follows:

### **"CROSS REFERENCE TO RELATED APPLICATION**

This application claims priority, under 35 U.S.C. 119(e), from provisional patent application serial number 60/339,734 filed on December 13, 2001. This application is a Division of and claims priority from U.S. Application Serial No. 10/290,616, filed on November 8, 2002, Attorney Docket No. YOR920020153US1.

This application is related to ~~application serial number~~ Application Serial No. 10/290,682, filed on November 8, 2002, \_\_\_\_\_, entitled "Improved Toughness, Adhesion and Smooth Metal Lines of Porous Low-k Dielectric Interconnect Structures," Attorney Docket No. YOR920020152US1, assigned to the same assignee as the present application, ~~and filed of even date herewith.~~"

Please amend the paragraph on page 2, lines 5-19, as follows:

"Many low-k dielectric plus Cu interconnect structures of the dual damascene type are known. For an example of the dual damascene process wherein SiLK<sup>TM</sup> dielectric material may be used as a low-k dielectric material, reference is made to United States Patent No. 6, 383, 920, which is assigned to the same assignee as the present invention, and is incorporated in its entirety by reference, as if fully set forth herein. In order to achieve the necessary reduction in the RC delay in future generations of integrated circuits, porous materials must be used as the dielectric. In addition, due to the 5-20 nanometer pore sizes of porous organic materials, a buried etch stop layer is necessary to give smooth metal line bottoms. These structures must go through several processing steps, including chemical mechanical polishing of the copper (CMP), which create stresses within the dielectric stack that can lead to delamination. The delamination can occur due to poor adhesion at the etch stop to

dielectric interfaces."

Please amend the paragraph on page 4, lines 5 to page 5, line 2, as follows:

"In accordance with the invention, an electrical interconnect structure on a substrate, comprises a first porous dielectric layer with surface region from which porogen has been removed; and an etch stop layer disposed upon the first porous dielectric layer so that the etch stop layer extends to partially fill pores in the surface region of the first porous dielectric layer from which the porogen has been removed. The structure may further comprise a second porous dielectric layer disposed upon the first porous dielectric layer. At least one of the first porous dielectric layer and the second porous dielectric layer may be comprised of ~~of~~ porous SiLK™ dielectric material, GX-3p™ dielectric material, or other porous low k dielectric materials where the porosity is formed from the decomposition of a sacrificial porogen, which may be a component of the material, as provided by the manufacturer. Materials of this kind are described in Patent Cooperation Treaty International Patent Application WO 00/31183 entitled A composition containing a cross-linkable matrix precursor and a porogen, and a porous matrix prepared therefrom of Kenneth, J. Bruza et al. which is assigned to The Dow Chemical Company, the contents of which are incorporated herein in their entirety by reference. The etch stop layer may be comprised of HOSP™ Dielectric Etch Stop, HOSP BEST™ Dielectric Etch Stop, ~~Ensemble~~ENSEMBLE™ Dielectric Etch Stop, ~~Ensemble~~ENSEMBLE™ Dielectric Hard Mask, organo silsesquioxanes, hydrido silsesquioxanes, hydrido-organosilsesquioxanes, siloxanes, or other spin-on material with etch selectivity to the porous dielectric. Materials of this kind are described in United States Patent US 6,218,020 entitled Dielectric films from organohydridosiloxane resins with high organic content of Nigel P. Hacker et al. which is assigned to AlliedSignal Inc., and United States Patent US 6,177,199 entitled Dielectric films from organohydridosiloxane resins with low organic content of Nigel P. Hacker et al. which is assigned to AlliedSignal Inc., the contents of which are incorporated herein in their entirety by reference."